



Low voltage fast-switching NPN power transistor

General features

- Very low collector-emitter saturation voltage
- High current gain characteristic
- Fast switching speed
- Miniature SOT-23 plastic package for surface mounting circuits
- In compliance with the 2002/93/EC European Directive

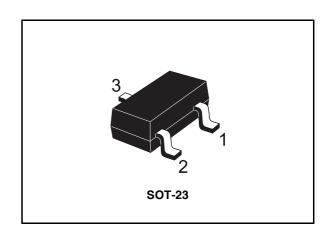
Description

The device is a NPN transistor manufactured using new "PB-HCD" (Power Bipolar High Current Density) technology. The resulting transistor shows exceptional high gain performances coupled with very low saturation voltage.

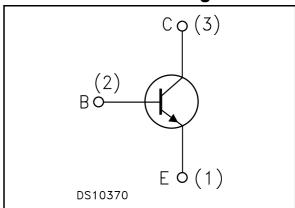
The complementary PNP is the 2STR2230.

Applications

- LED
- Motherboard & hard disk drive
- Mobile equipment
- Battery charger
- Voltage regulation



Internal schematic diagram



Order codes

Part Number	Marking	Package	Packing
2STR1230	130	SOT-23	Tape & reel

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2STR1230 Electrical ratings

1 Electrical ratings

Table 1. Absolute maximum rating

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{CE} = 0)	30	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	30	V
V _{EBO}	Emitter-base voltage (I _C = 0)	5	V
I _C	Collector current	1.5	Α
I _{CM}	Collector peak current (t _P < 5ms)	3	Α
P _{tot}	Total dissipation at T _{amb} = 25°C	0.5	W
T _{stg}	Storage temperature	-65 to 150	°C
T _J	Max. operating junction temperature	150	°C

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-amb} ⁽¹⁾	Thermal resistance junction-amb max	250	°C/W

⁽¹⁾ Device mounted on PCB area of $1\,\mathrm{cm}^2$

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Electrical characteristics 2STR1230

2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$

Table 3. Electrical characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E =0)	V _{CB} = 30V			0.1	μА
I _{EBO}	Emitter cut-off current (I _C =0)	V _{EB} = 4V			0.1	μΑ
V _{(BR)CBO}	Collector-emitter breakdown voltage (I _E = 0)	I _C = 100μA	30			V
V _{(BR)CEO} (2)	Collector-emitter breakdown voltage (I _B = 0)	I _C = 10mA	30			٧
V _{(BR)EBO}	Emitter-base breakdown voltage (I _C = 0)	I _E = 100μA	5			V
V _{CE(sat)} (2)	Collector-emitter saturation voltage	$I_C = 0.1A$ $I_B = 1mA$ $I_C = 1A$ $I_B = 100mA$ $I_C = 2A$ $I_B = 200mA$		0.25 0.4	0.15 0.5 0.85	V V V
V _{BE(sat)} (2)	Base-emitter saturation voltage	I _C = 1A I _B = 100mA		0.9	1.25	V
h _{FE} ⁽²⁾	DC current gain	$\begin{split} & I_{C} = 50 \text{mA} & V_{CE} = 2V \\ & I_{C} = 0.5 \text{A} & V_{CE} = 2V \\ & I_{C} = 1 \text{A} & V_{CE} = 2V \\ & I_{C} = 2 \text{A} & V_{CE} = 2V \end{split}$	210 180 130 80	280	560	
C _{CBO}	Collector-base capacitance	I _E = 0 V _{CB} = 10V f = 1MHz		3		pF
t _{on}	Resistive load Turn-on time Turn-off time	$I_C = 1.5A$ $V_{CC} = 10V$ $I_{B1} = -I_{B2} = 150mA$		70 380		ns ns

Note (2) Pulsed duration = 300 μ s, duty cycle \leq 1.5%

2.1 Electrical characteristics (curves)

Figure 1. DC current gain

T_J=125 °C

T_J=-40°C

T_J=25 °C

V_{CE}=2V

10
0.001 0.01 0.1 1 l_C (A)

Figure 2. Collector-emitter saturation voltage

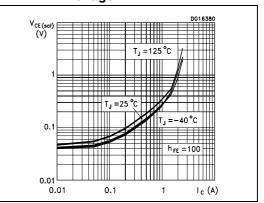
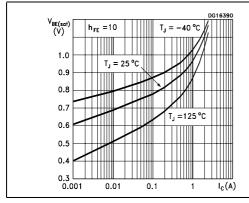


Figure 3. Base-emitter saturation voltage

Figure 4. Resistive load switching time



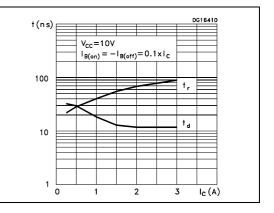
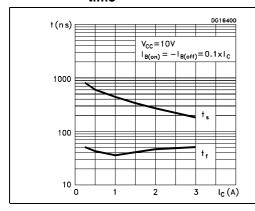
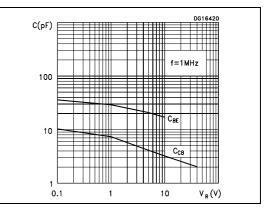


Figure 5. Resistive load switching time

Figure 6. Capacitance

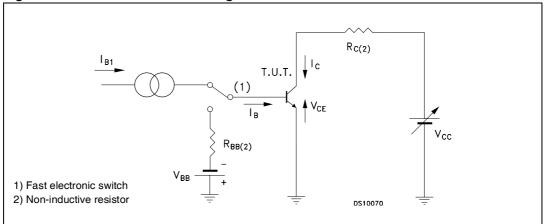




Electrical characteristics 2STR1230

2.2 Test circuits

Figure 7. Resistive load switching test circuit

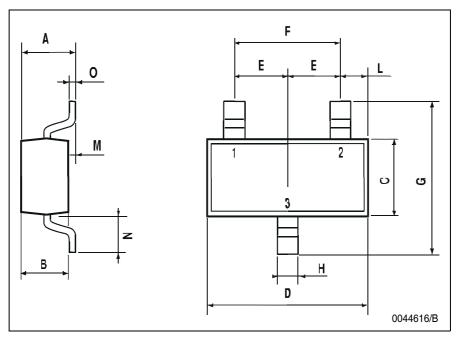


3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

SOT-23 MECHANICAL DATA

DIM.	mm			mils		
Dim.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	0.85		1.1	33.4		43.3
В	0.65		0.95	25.6		37.4
С	1.20		1.4	47.2		55.1
D	2.80		3	110.2		118
Е	0.95		1.05	37.4		41.3
F	1.9		2.05	74.8		80.7
G	2.1		2.5	82.6		98.4
Н	0.38		0.48	14.9		18.8
L	0.3		0.6	11.8		23.6
М	0		0.1	0		3.9
N	0.3		0.65	11.8		25.6
0	0.09		0.17	3.5		6.7



2STR1230 Revision history

4 Revision history

Table 4. Revision history

Date	Revision	Changes
18-Jul-2006	1	Initial release
24-Oct-2006	2	New graphics

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